

# EE236: Experiment No. 8

## P-channel MOSFET I-V Characteristics

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## 1 Overview of the experiment

### 1.1 Aim of the experiment

- Measuring output and transfer characteristics of a P-channel enhancement type MOSFET (also called PMOS).
- Investigating the effect of body bias on the characteristics of the PMOS.

### 1.2 Methods

- Obtaining the values of  $V_t$  and  $g_m$  using the plot of linear Transfer Characteristics of the mosfet.

$$g_m = \left. \frac{d(I_D)}{d(V_{SG})} \right|_{at\,const\,V_{SD}} \quad (1)$$

- finding the output resistance  $r_o$  using the slope of the plot of  $I_D$  vs  $V_{SD}$  for drain characteristics.

$$r_o = \left. \frac{d(V_{SD})}{d(I_D)} \right|_{at\,const\,V_{SG}} \quad (2)$$

- finding the body effect co-efficient by plotting  $V_T$  vs  $V_{sb}$  by changing the  $V_{sb}$ .
- $V_T = V_{T_o} + \gamma(\sqrt{si(s)} - \sqrt{si(s)})$

## 2 Design

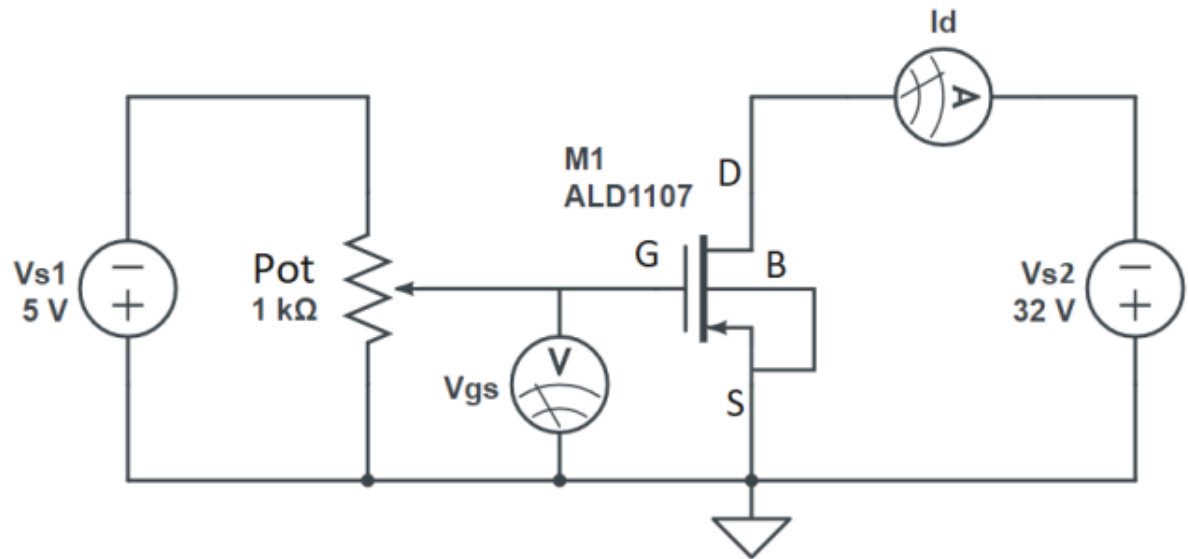


Figure 1: Circuit for linear transfer characteristics and drain characteristics

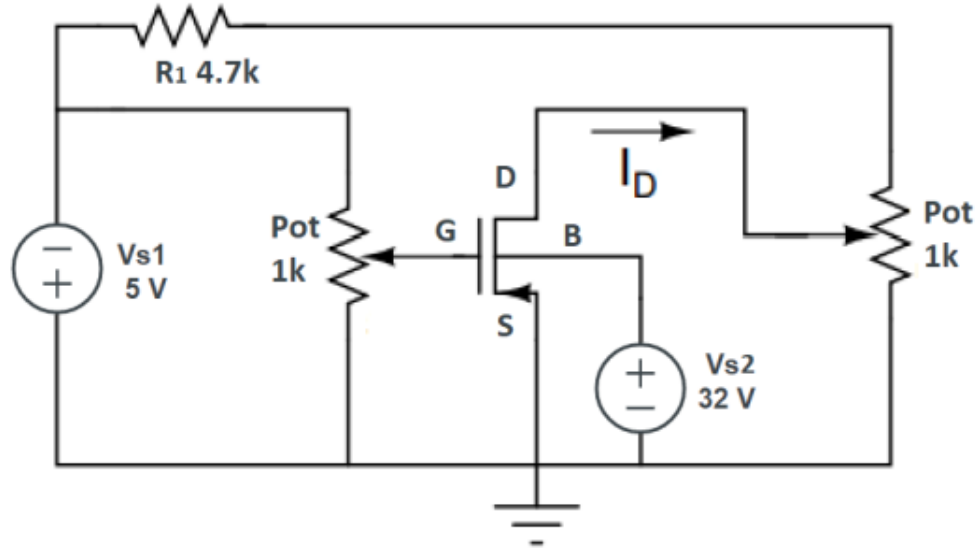


Figure 2: PMOS body effect circuit.

## 2.1 Experimental results

$g_m = 4/0.15 = 13.35$ .  $r_0 = 0.5/0.59 = 0.81$ .  $\gamma = 0.397$ .

part(1)

```

VSD = 5V VSD = .2V
ID      VSG      ID      VSG
0       0.07     0       0.2
0       0.58     0       0.799
0       0.9      0.072 1.89
0.015 1      0.082 2.07
0.038 1.19 0.095 2.3
0.045 1.23 0.106 2.54
0.063 1.34 0.119 2.82
0.121 1.59 0.128 3
0.157 1.72 0.136 3.23
0.215 1.91 0.152 3.61
0.293 2.13 0.165 4.14
0.319 2.19 0.178 4.38

```

0.352	2.28	0.184	4.6
0.4	2.4	0.191	4.81
0.638	2.91	0.193	4.88
0.829	3.28	0.196	4.97
0.953	3.5		
1.245	3.99		
1.376	4.19		
1.543	4.45		
1.9	4.97		

part(2)

Vsd	Id1	Id2	Id3
0.02	0.005		
0.27	0.051		
0.48	0.073		
0.59	0.079		
0.74	0.083		
0.85	0.085		
1.93	0.092		
2.07	0.093		
3.51	0.099		
3.78	0.1		
4	0.101		
4.33	0.102		
4.72	0.103		
5.05	0.104		
0.02	0.01		
0.19	0.084		
0.28	0.122		
0.35	0.146		
0.39	0.162		
0.63	0.24		
0.75	0.273		
0.92	0.311		
1.46	0.383		

2.14 0.406  
 2.64 0.416  
 3.08 0.423  
 3.72 0.432  
 4.21 0.438  
 4.45 0.44  
 5.05 0.447  
 0.02 0.014  
 0.19 0.124  
 0.3 0.185  
 0.42 0.257  
 0.53 0.312  
 0.58 0.342  
 0.73 0.415  
 0.96 0.518  
 1.21 0.618  
 1.4 0.681  
 1.9 0.807  
 2.55 0.883  
 2.76 0.895  
 3.07 0.909  
 3.74 0.932  
 3.98 0.939  
 4.63 0.955  
 4.91 0.961  
 5.02 0.963

Part(3)

$V_{sg} \ V_{sb} = -1$   
 0.01 0  
 0.95 0  
 0.984 0.001  
 1.14 0.005  
 1.18 0.008  
 1.25 0.012

1.38	0.019
1.48	0.025
1.56	0.029
1.73	0.04
2.05	0.055
2.2	0.064
2.49	0.077
2.83	0.09
3.13	0.099
3.69	0.115
3.87	0.12
4.47	0.144
4.88	0.159
5	0.165

Vsg	Vsb = -2
0.01	0
0.1	0
1.07	0
1.09	0.001
1.24	0.005
1.34	0.01
1.41	0.014
1.53	0.021
1.67	0.028
1.8	0.034
2.08	0.054

2.22	0.056
2.47	0.066
2.63	0.076
2.84	0.084
3.12	0.093
3.32	0.1
3.51	0.112
3.75	0.119
3.98	0.126
4.14	0.13

4.55 0.14  
 4.72 0.144  
 5 0.15

Vgs                      Vsb = -3  
 0.01 0  
 0.39 0  
 1.18 0  
 1.195 0.001  
 1.26 0.002  
 1.39 0.008  
 1.47 0.012  
 1.67 0.022  
 1.85 0.032  
 1.99 0.038  
 2.19 0.046  
 2.51 0.065  
 2.76 0.074  
 3.2 0.09  
 3.39 0.1  
 3.67 0.108  
 3.97 0.116  
 4.18 0.122  
 4.51 0.13  
 5 0.141

Vsb Vt gamma  
 0 0.78  
 -1 0.958 0.398020099994962

-2 1.09 0.39800082283055  
-3 1.195 0.39339040496137

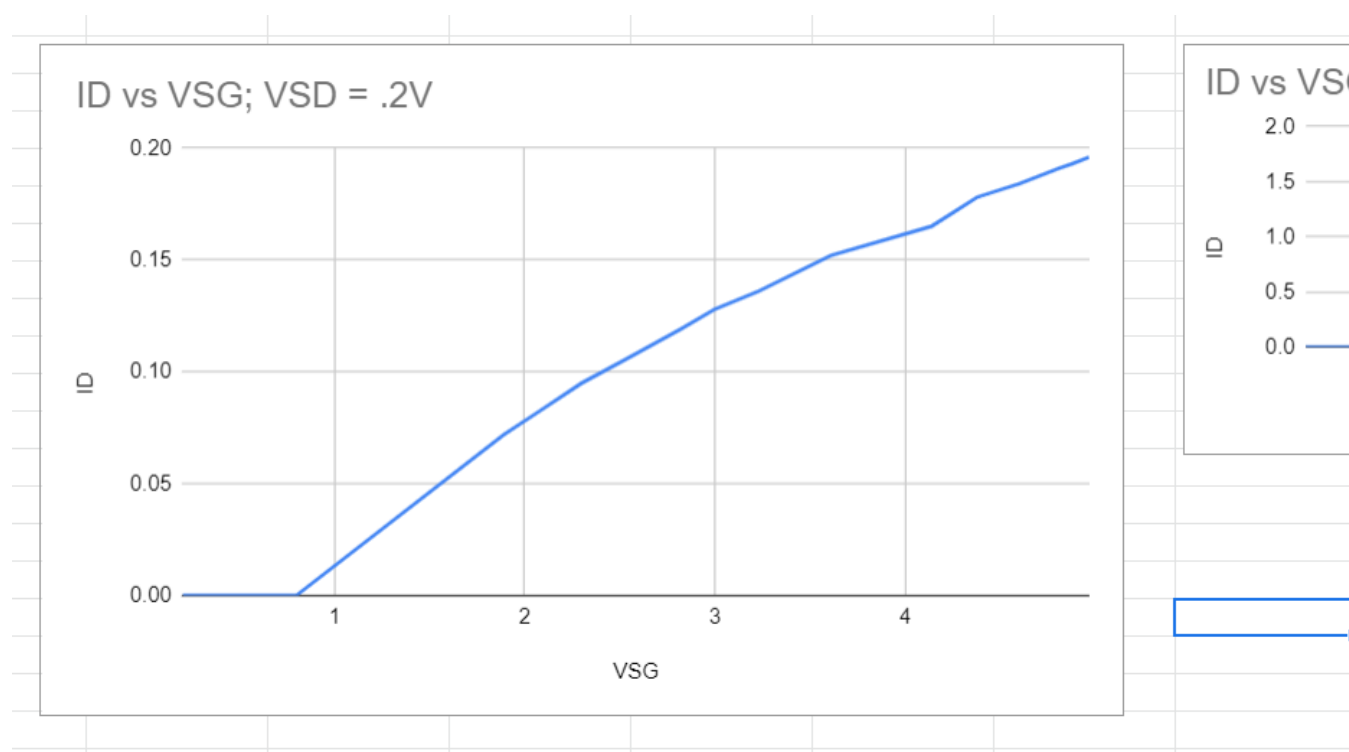


Figure 3:  $I_D$  vs  $V_{SG}$



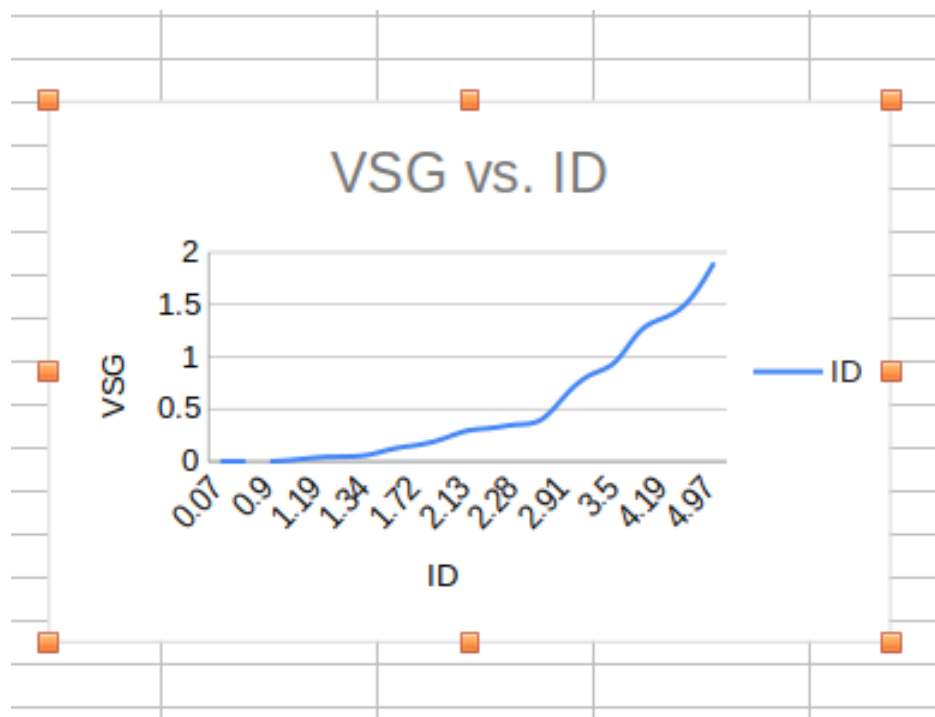


Figure 4: Vsd vs Id

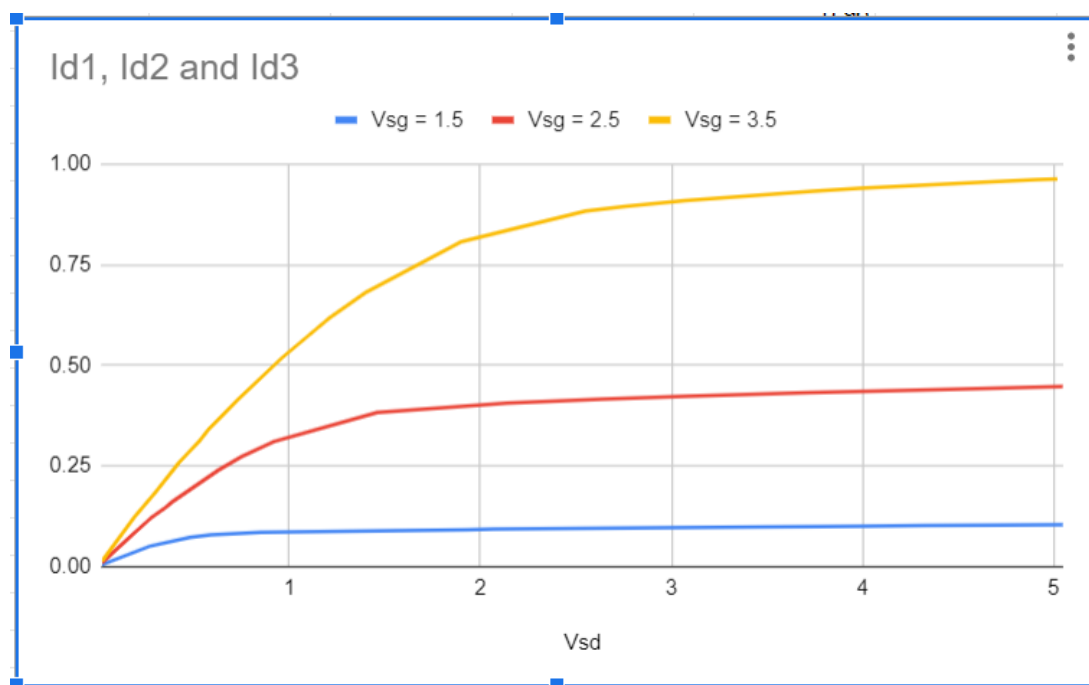


Figure 5: part2

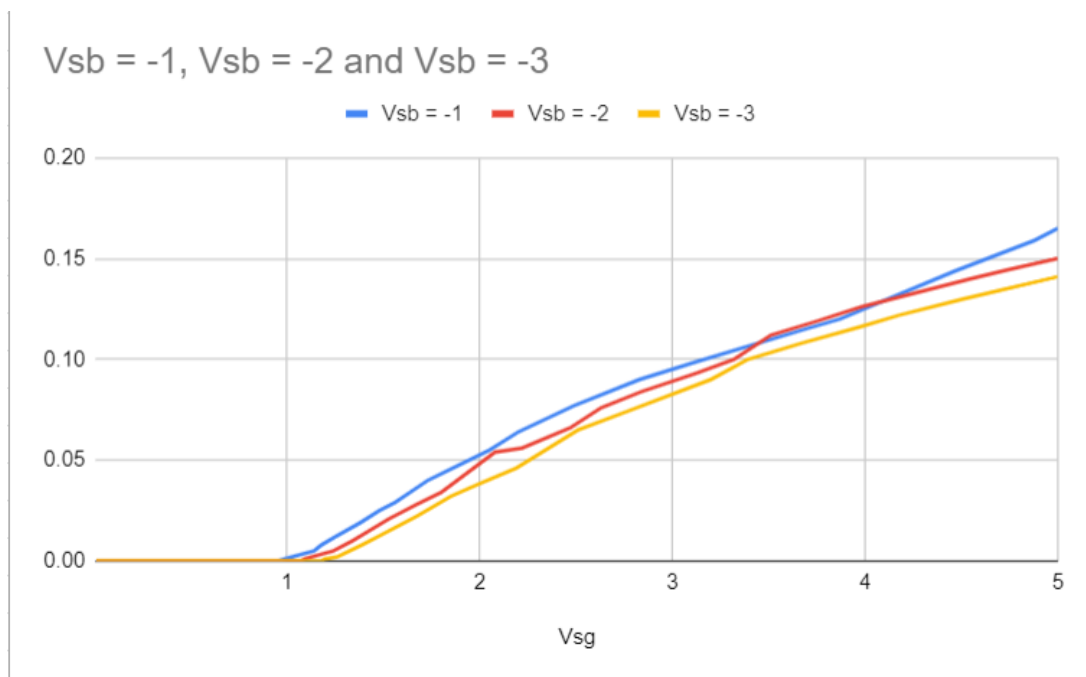


Figure 6: Part 3 -  $I_D$  vs  $V_{SG}$

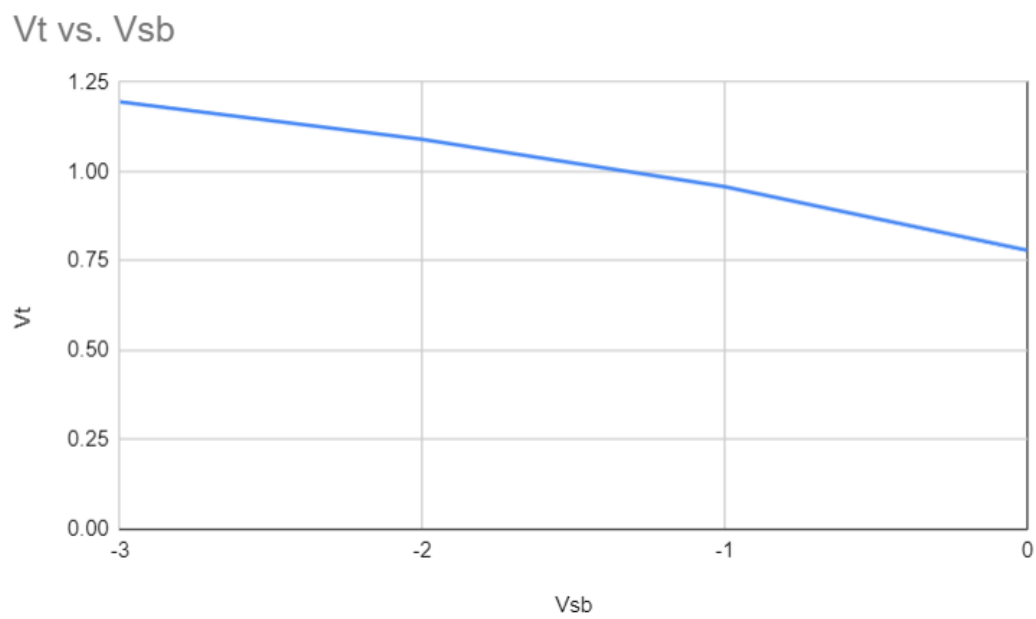


Figure 7: Part 3 -  $V_t$  vs  $V_{sb}$